

Features

- ☐ Fast 8192 x 8 bit static CMOS RAM
- ☐ 35 ns Access Time
- ☐ Bidirectional data inputs and data outputs
- ☐ Three-state outputs
- ☐ Data retention current at 3 V: < 50 μ A
- ☐ Standby current < 100 μ A
- ☐ TTL/CMOS-compatible
- ☐ Automatic reduction of power dissipation in long Read or Write cycles
- ☐ Power supply voltage 5 V
- ☐ Operating temperature range -40 to 125 $^{\circ}$ C
- ☐ Quality assessment according to CECC 90000, CECC 90100 and CECC 90111
- ☐ ESD protection > 2000 V (MIL STD 883C M3015.7)
- ☐ Latch-up immunity > 200 mA
- ☐ Package: SOP28 (300 mil)

Description

The U62H64SA is a static RAM manufactured using a CMOS process technology with the following operating modes:

- Read
- Standby
- Write
- Data Retention

The memory array is based on a 6-transistor cell.

The circuit is activated by the rising edge of E2 (at $\overline{E1} = L$), or the falling edge of $\overline{E1}$ (at E2 = H). The address and control inputs open simultaneously.

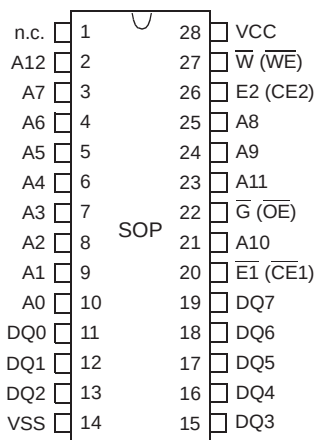
According to the information of $\overline{W}$ and $\overline{G}$, the data inputs, or outputs, are active. During the active state ($\overline{E1} = L$ and E2 = H), each address change leads to a new Read or Write cycle. In a Read cycle, the data outputs are activated by the falling edge of $\overline{G}$, afterwards the data word read will be available at

the outputs DQ0 - DQ7. After the address change, the data outputs go High-Z until the new read information is available. The data outputs have no preferred state. If the memory is driven by CMOS levels in the active state, and if there is no change of the address, data input and control signals $\overline{W}$ or $\overline{G}$, the operating current (at $I_O = 0$ mA) drops to the value of the operating current in the Standby mode. The Read cycle is finished by the falling edge of E2 or $\overline{W}$, or by the rising edge of $\overline{E1}$, respectively.

Data retention is guaranteed down to 2 V.

With the exception of $\overline{E1}$ and E2, all inputs consist of NOR gates, so that no pull-up/pull-down resistors are required. This gate circuit allows to achieve low power standby requirements by activation with TTL-levels too.

Pin Configuration

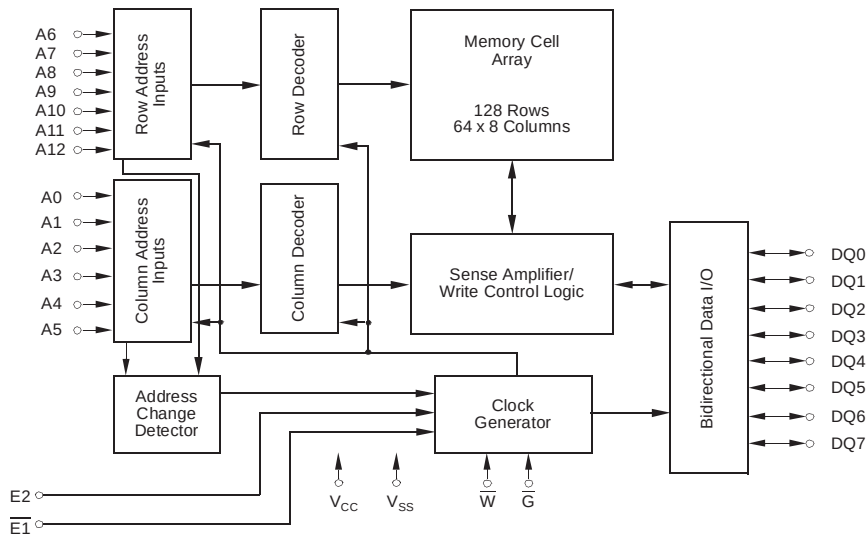


Top View

Pin Description

Signal Name	Signal Description
A0 - A12	Address Inputs
DQ0 - DQ7	Data In/Out
$\overline{E1}$	Chip Enable 1
E2	Chip Enable 2
$\overline{G}$	Output Enable
$\overline{W}$	Write Enable
VCC	Power Supply Voltage
VSS	Ground
n.c.	not connected

Block Diagram



Truth Table

Operating Mode	$\overline{E1}$	E2	$\overline{W}$	$\overline{G}$	DQ0 - DQ7
Standby/not selected	*	L	*	*	High-Z
	H	*	*	*	High-Z
Internal Read	L	H	H	H	High-Z
Read	L	H	H	L	Data Outputs Low-Z
Write	L	H	L	*	Data Inputs High-Z

* H or L

Characteristics

All voltages are referenced to $V_{SS} = 0$ V (ground).
All characteristics are valid in the power supply voltage range and in the operating temperature range specified.
Dynamic measurements are based on a rise and fall time of ≤ 5 ns, measured between 10 % and 90 % of V_I , as well as input levels of $V_{IL} = 0$ V and $V_{IH} = 3$ V. The timing reference level of all input and output signals is 1.5 V, with the exception of the t_{dis} -times and t_{en} -times, in which cases transition is measured ± 200 mV from steady-state voltage.

Maximum Ratings	Symbol	Min.	Max.	Unit
Power Supply Voltage	V_{CC}	-0.3	7	V
Input Voltage	V_I	-0.3	$V_{CC} + 0.5$	V
Output Voltage	V_O	-0.3	$V_{CC} + 0.5$	V
Operating Temperature	T_a	-40	125	°C
Storage Temperature	T_{stg}	-65	150	°C
Output Short-Circuit Current at $V_{CC} = 5$ V and $V_O = 0$ V*	$ I_{OS} $		200	mA

* Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 s.

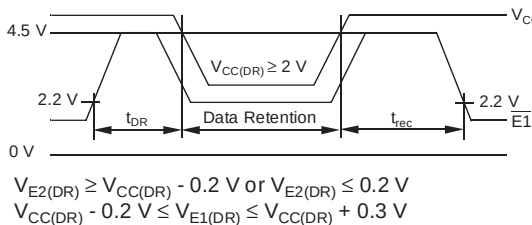
Recommended Operating Conditions	Symbol	Conditions	Min.	Max.	Unit
Power Supply Voltage	V_{CC}		4.5	5.5	V
Data Retention Voltage	$V_{CC(DR)}$		2.0	-	V
Input Low Voltage *	V_{IL}		-0.3	0.8	V
Input High Voltage	V_{IH}		2.2	$V_{CC}+0.3$	V

* -2 V at Pulse Width 10 ns or -1 V at Pulse Width 50 ns

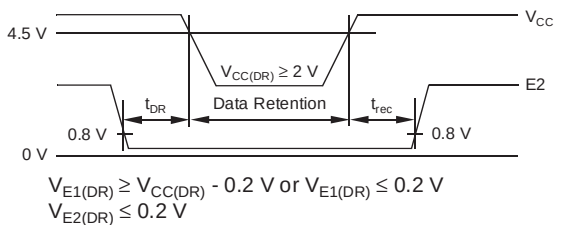
Electrical Characteristics	Symbol	Conditions	Min.	Max.	Unit
Supply Current - Operating Mode	$I_{CC(OP)}$	$V_{CC} = 5.5 \text{ V}$ $V_{IL} = 0.8 \text{ V}$ $V_{IH} = 2.2 \text{ V}$ $t_{cW} = 35 \text{ ns}$		50	mA
Supply Current - Standby Mode (CMOS level)	$I_{CC(SB)}$	$V_{CC} = 5.5 \text{ V}$ $V_{E1} = V_{E2} = V_{CC} - 0.2 \text{ V}$		100	μA
Supply Current - Standby Mode (TTL level)	$I_{CC(SB)1}$	$V_{CC} = 5.5 \text{ V}$ $V_{E1} = V_{E2} = 2.2 \text{ V}$		5 (typ. 2)	mA
Supply Current - Data Retention Mode	$I_{CC(DR)}$	$V_{CC(DR)} = 3.0 \text{ V}$ $V_{E1} = V_{E2} = V_{CC(DR)} - 0.2 \text{ V}$		50	μA
Output High Voltage	V_{OH}	$V_{CC} = 4.5 \text{ V}$ $I_{OH} = -4.0 \text{ mA}$	2.4	-	V
Output Low Voltage	V_{OL}	$V_{CC} = 4.5 \text{ V}$ $I_{OL} = 8.0 \text{ mA}$	-	0.4	V
Output High Current	I_{OH}	$V_{CC} = 4.5 \text{ V}$ $V_{OH} = 2.4 \text{ V}$	-	-4.0	mA
Output Low Current	I_{OL}	$V_{CC} = 4.5 \text{ V}$ $V_{OL} = 0.4 \text{ V}$	8.0	-	mA
Input High Leakage Current	I_{IH}	$V_{CC} = 5.5 \text{ V}$ $V_{IH} = 5.5 \text{ V}$	-	2	μA
Input Low Leakage Current	I_{IL}	$V_{CC} = 5.5 \text{ V}$ $V_{IL} = 0 \text{ V}$	-2	-	μA
Output Leakage Current High at Three-State Outputs	I_{OHZ}	$V_{CC} = 5.5 \text{ V}$ $V_{OH} = 5.5 \text{ V}$	-	2	μA
Low at Three-State Outputs	I_{OLZ}	$V_{CC} = 5.5 \text{ V}$ $V_{OL} = 0 \text{ V}$	-2	-	μA

Switching Characteristics	Symbol		Min.	Max.	Unit
	Alt.	IEC	35	35	
Time to Output in Low-Z from $\overline{E1}$ LOW or E2 HIGH $\overline{G}$ LOW $\overline{W}$ HIGH	t_{LZCE} t_{LZOE} t_{LZWE}	$t_{en(E)}$ $t_{en(G)}$ $t_{en(W)}$	5 0 0		ns ns ns
Cycle Time Write Cycle Time Read Cycle Time	t_{WC} t_{RC}	t_{cW} t_{cR}	35 35		ns ns
Access Time $\overline{E1}$ LOW or E2 HIGH to Data Valid $\overline{G}$ LOW to Data Valid Address to Data Valid	t_{ACE} t_{OE} t_{AA}	$t_{a(E)}$ $t_{a(G)}$ $t_{a(A)}$		35 15 35	ns ns ns
Pulse Widths Write Pulse Width Chip Enable to End of Write	t_{WP} t_{CW}	$t_{w(W)}$ $t_{w(E)}$	20 25		ns ns
Setup Times Address Setup Time Chip Enable to End of Write Write Pulse Width Data Setup Time	t_{AS} t_{CW} t_{WP} t_{DS}	$t_{su(A)}$ $t_{su(E)}$ $t_{su(W)}$ $t_{su(D)}$	0 25 20 15		ns ns ns ns
Data Hold Time Address Hold from End of Write	t_{DH} t_{AH}	$t_{h(D)}$ $t_{h(A)}$	0 0		ns ns
Output Hold Time from Address Change	t_{OH}	$t_{v(A)}$	5		ns
$\overline{E1}$ HIGH or E2 LOW to Output in High-Z $\overline{W}$ LOW to Output in High-Z $\overline{G}$ HIGH to Output in High-Z	t_{HZCE} t_{HZWE} t_{HZOE}	$t_{dis(E)}$ $t_{dis(W)}$ $t_{dis(G)}$		15 15 12	ns ns ns
$\overline{E1}$ LOW or E2 HIGH to Power-Up	t_{PU}		0		ns
$\overline{E1}$ HIGH or E2 LOW to Power-Down	t_{PD}			35	ns

Data Retention Mode $\overline{E1}$ -Controlled



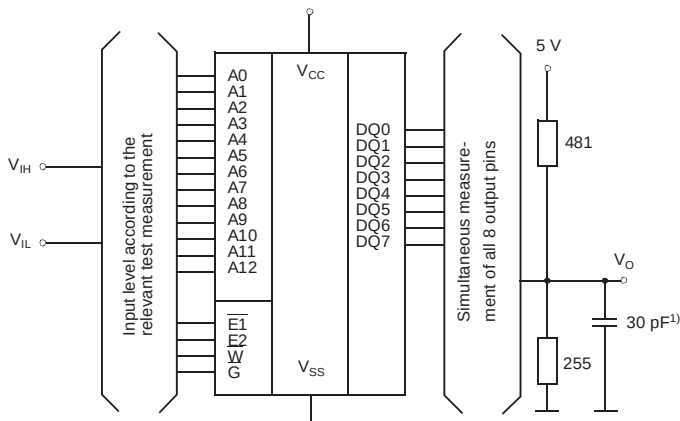
Data Retention Mode E2-Controlled



Chip Deselect to Data Retention Time
Operating Recovery Time at $V_{CC(DR)}$

t_{DR} : min 0 ns
 t_{rec} : min t_{cR}

Test Configuration for Functional Check



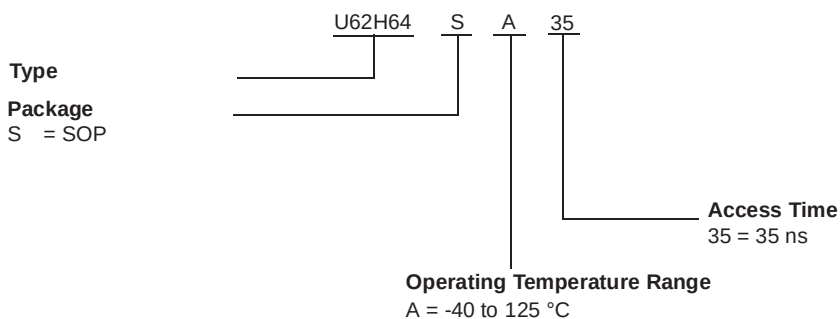
¹⁾ In measurement of $t_{dis(E)}$, $t_{dis(W)}$, $t_{dis(G)}$, $t_{en(E)}$, $t_{en(W)}$, $t_{en(G)}$ the capacitance is 5 pF.

Capacitance	Conditions	Symbol	Min.	Max.	Unit
Input Capacitance	$V_{CC} = 5.0 \text{ V}$ $V_I = V_{SS}$	C_I		8	pF
Output Capacitance	$f = 1 \text{ MHz}$ $T_a = 25^\circ \text{C}$	C_O		10	pF

All pins not under test must be connected with ground by capacitors.

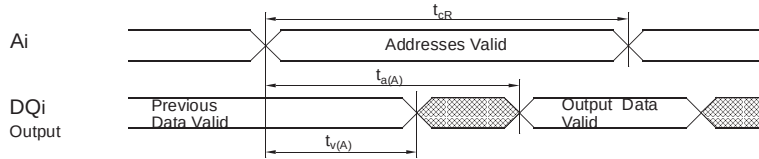
IC Code Number

Example

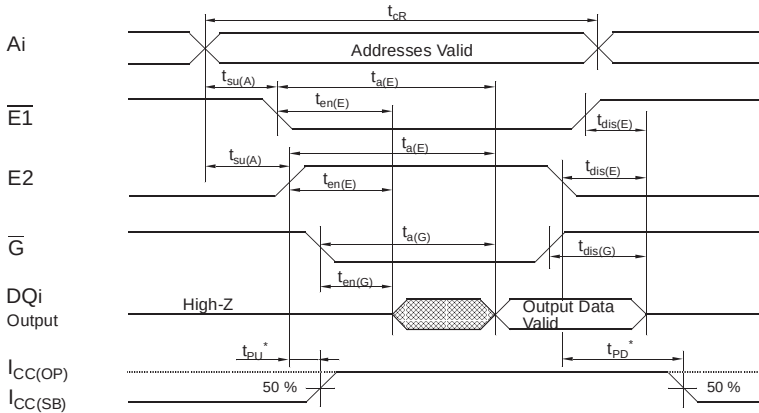


The date of manufacture is given by the last 4 digits of the mark, the first 2 digits indicating the year, and the last 2 digits the calendar week.

Read Cycle 1 (during Read cycle: $\overline{E1} = \overline{G} = V_{IL}$, $E2 = \overline{W} = V_{IH}$, A_i -controlled)

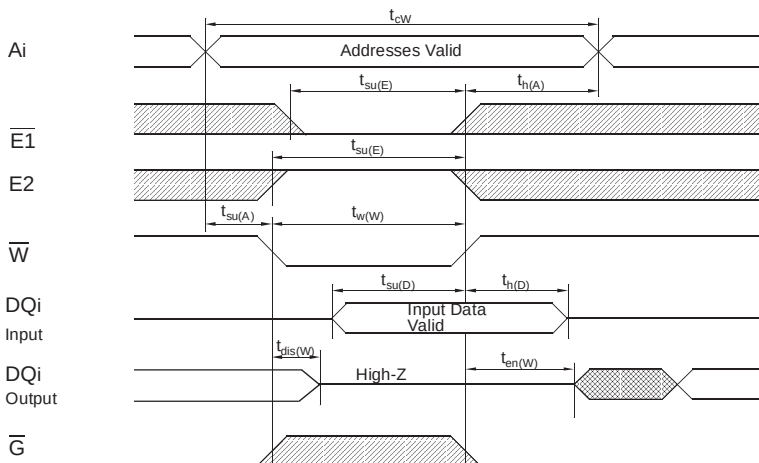


Read Cycle 2 (during Read cycle: $\overline{W} = V_{IH}$, $\overline{G}$ -, $\overline{E1}$ - or $E2$ -controlled)

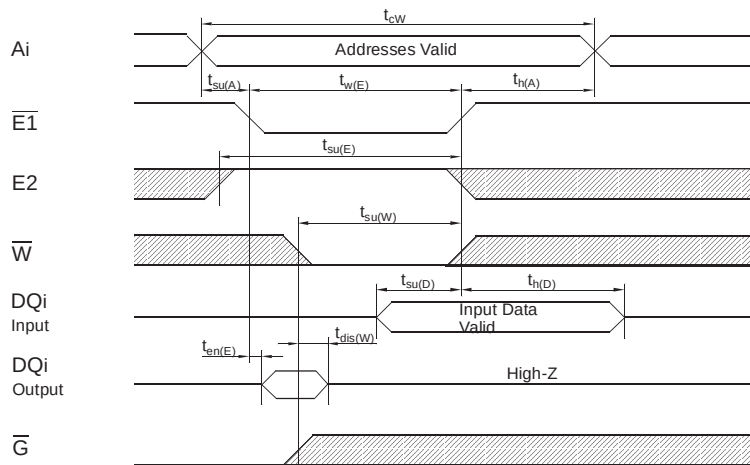


* The same applies to $\overline{E1}$

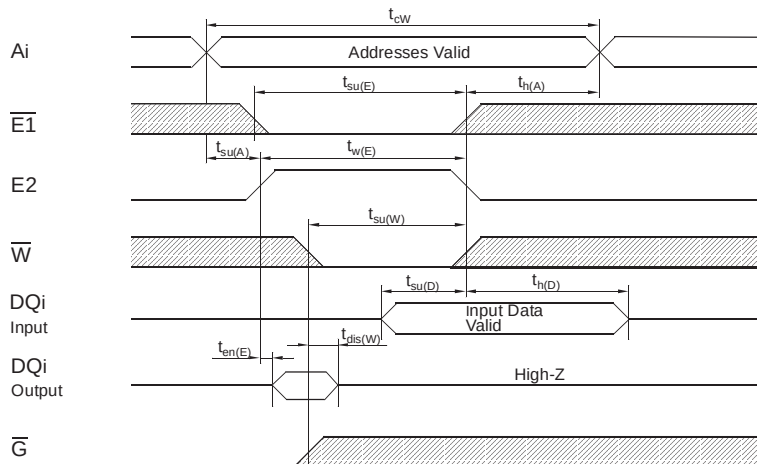
Write Cycle 1 ($\overline{W}$ -controlled)



Write Cycle 2 ($\overline{E1}$ -controlled)



Write Cycle 3 (E2-controlled)



undefined



L- or H-level



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